

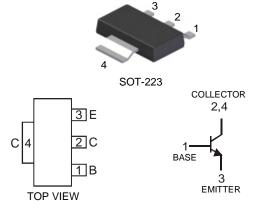


# NPN SURFACE MOUNT TRANSISTOR

DZT5551

#### Features

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DZT5401)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 3)
- **Mechanical Data**
- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)



Schematic and Pin Configuration

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	Ιc	600	mA

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation $@T_A = 25^{\circ}C$ (Note 3)	PD	1	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 3)	$R_{ ext{ heta}JA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)			•		·
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	180	_	V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	160	_	V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	50	nA μA	$V_{CB} = 120V, I_E = 0$ $V_{CB} = 120V, I_E = 0, T_A = 100^{\circ}C$
Emitter Cutoff Current	I <sub>EBO</sub>		50	nA	$V_{EB} = 4.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)					• == · · •
DC Current Gain	hFE	80 80 30	250 —	—	$\begin{split} I_{C} &= 1.0 \text{mA}, \ V_{CE} = 5.0 \text{V} \\ I_{C} &= 10 \text{mA}, \ V_{CE} = 5.0 \text{V} \\ I_{C} &= 50 \text{mA}, \ V_{CE} = 5.0 \text{V} \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.15 0.20	V	$I_{C} = 10$ mA, $I_{B} = 1.0$ mA $I_{C} = 50$ mA, $I_{B} = 5.0$ mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	1.0	V	$I_{C} = 10mA$ , $I_{B} = 1.0mA$ $I_{C} = 50mA$ , $I_{B} = 5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>	_	6.0	pF	$V_{CB} = 10V$ , f = 1.0MHz, I <sub>E</sub> = 0
Small Signal Current Gain	h <sub>fe</sub>	50	200		V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	300	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF		8.0	dB	$V_{CE} = 5.0V$ , $I_C = 200\mu A$ , $R_S = 1.0k\Omega$ , $f = 1.0kHz$

1. No purposefully added lead.

2

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our 3. website at http://www.diodes.com/datasheets/ap02001.pdf.

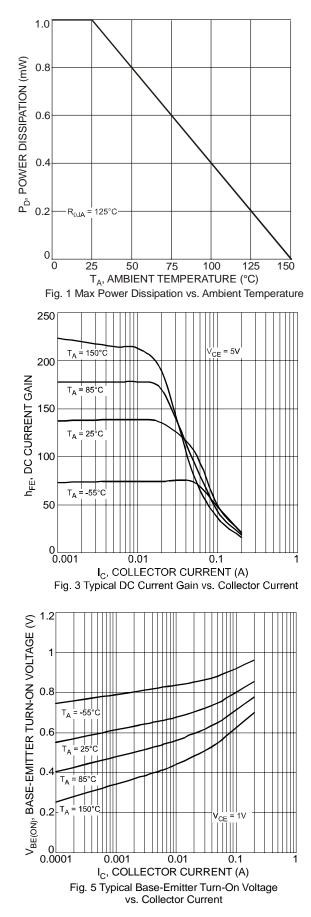
4. Measured under pulsed conditions. Pulse width =  $300\mu$ s. Duty cycle  $\leq 2\%$ .

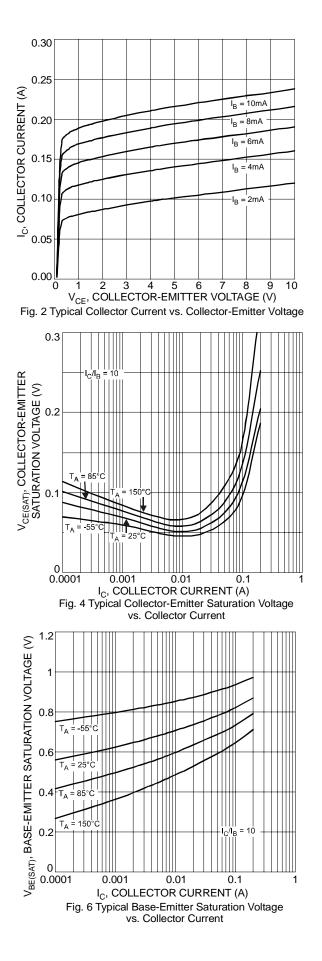
DS31219 Rev. 2 - 2

Downloaded from Elcodis.com electronic components distributor

Notes:

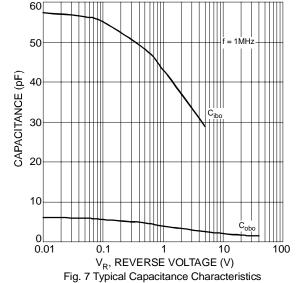


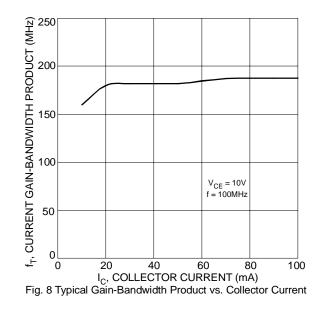




NEW PRODUCT





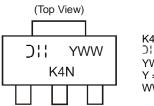


## Ordering Information (Note 5)

Device	Packaging	Shipping
DZT5551-13	SOT-223	2500/Tape & Reel

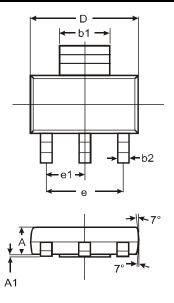
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

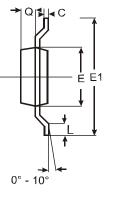
## **Marking Information**



K4N = Product type marking code DII = Manufacturer's code marking YWW = Date code marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

# Package Outline Dimensions



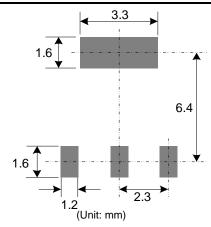


SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1			2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

DS31219 Rev. 2 - 2



### **Suggested Pad Layout**



#### IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

#### LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.